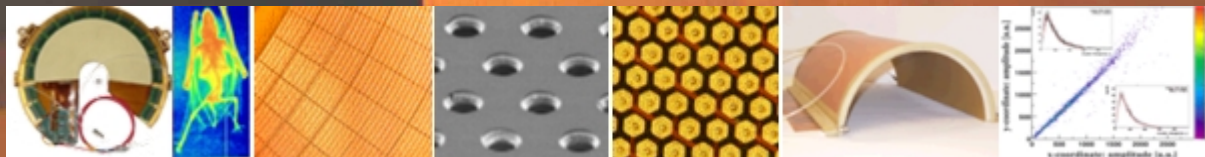


GEM at CERN

Leszek Ropelewski CERN PH-DT2-ST & TOTEM



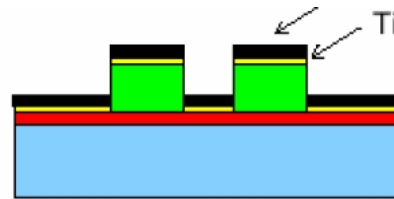
MicroStrip Gas Chamber

Semiconductor industry technology:

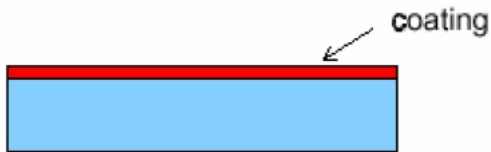
Photolithography
Etching
Coating
Doping



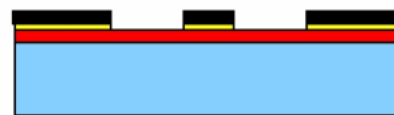
SUBSTRATE CLEANING



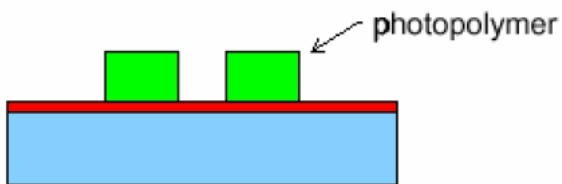
METAL DEPOSITION



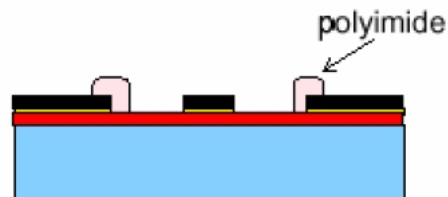
COATING



LIFT-OFF PROCESS

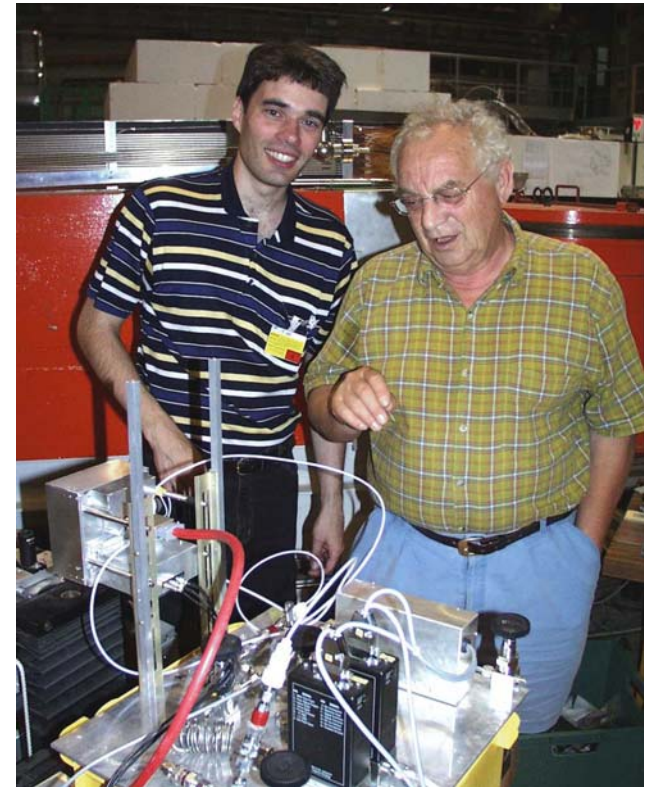


PHOTOLITHOGRAPHIC PROCESS
AND PLASMA CLEANING



EDGE PASSIVATION

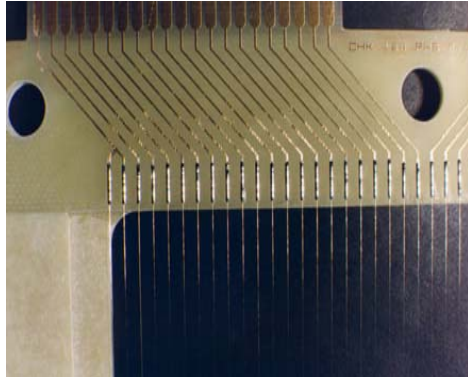
Lift-off technique



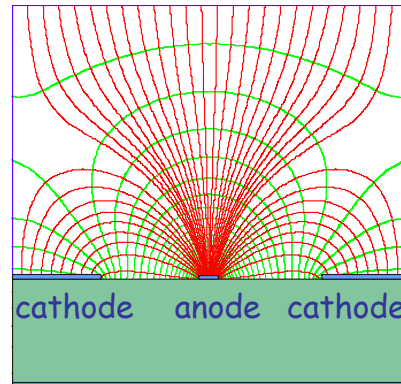
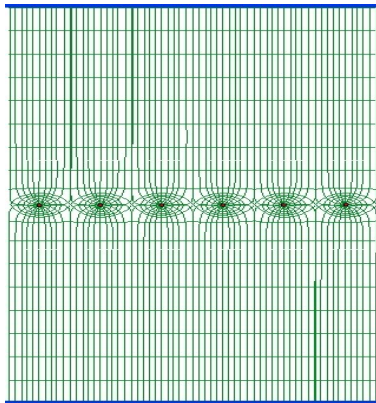
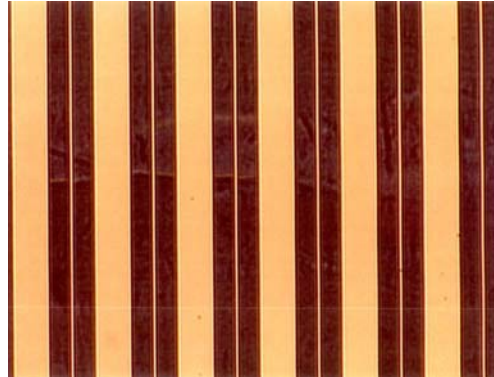
A. Oed
Nucl. Instr. and Meth. A263 (1988) 351.

MicroStrip Gas Chamber

MWPC

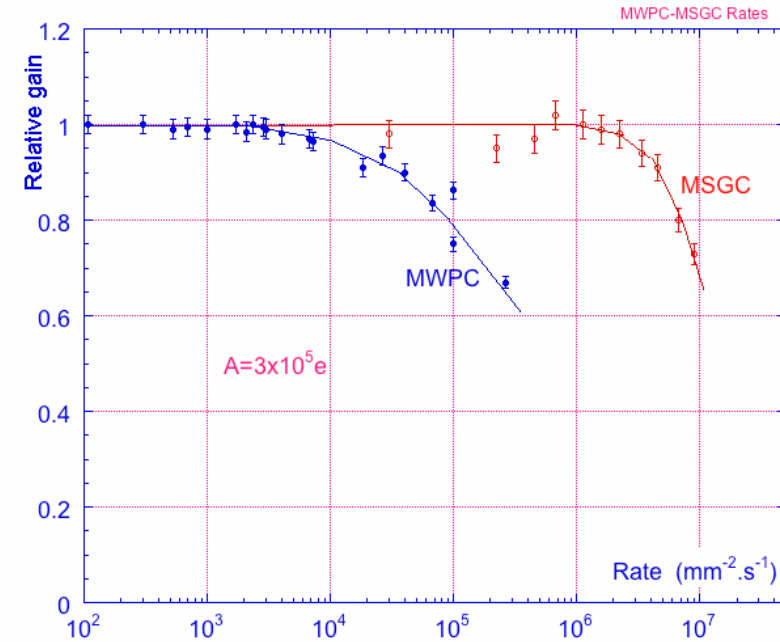


MSGC



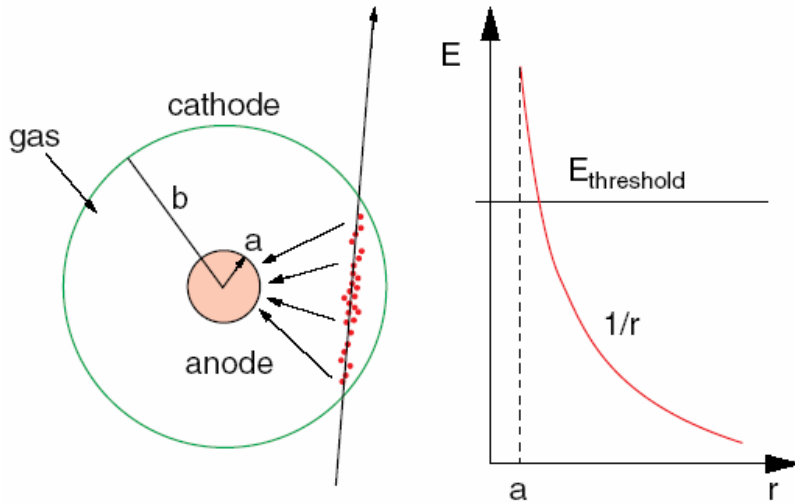
Typical distance between wires limited to 1 mm due to mechanical and electrostatic forces

Typical distance between anodes 200 μm thanks to semiconductor etching technology

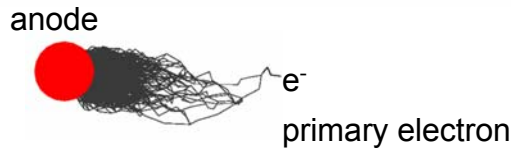


Rate capability limit due to space charge overcome by increased amplifying cell granularity

Single Wire Proportional Chamber



Electrons liberated by ionization drift towards the anode wire.
 Electrical field close to the wire (typical wire \varnothing ~few tens of μm) is sufficiently high for electrons (above 10 kV/cm) to gain enough energy to ionize further \rightarrow **avalanche** - exponential increase of number of electron ion pairs.



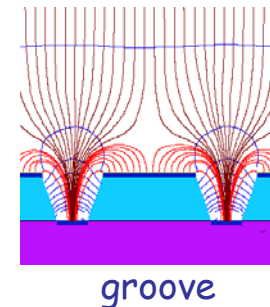
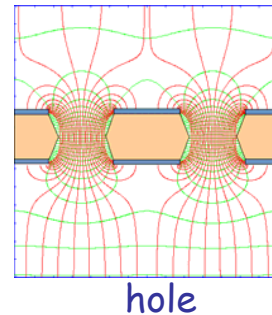
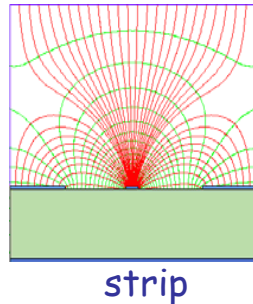
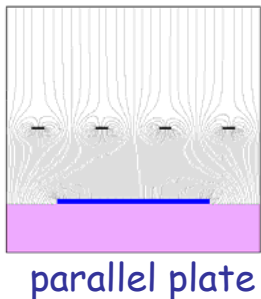
JV_2816

$$E(r) = \frac{CV_0}{2\pi\epsilon_0} \cdot \frac{1}{r}$$

C – capacitance/unit length

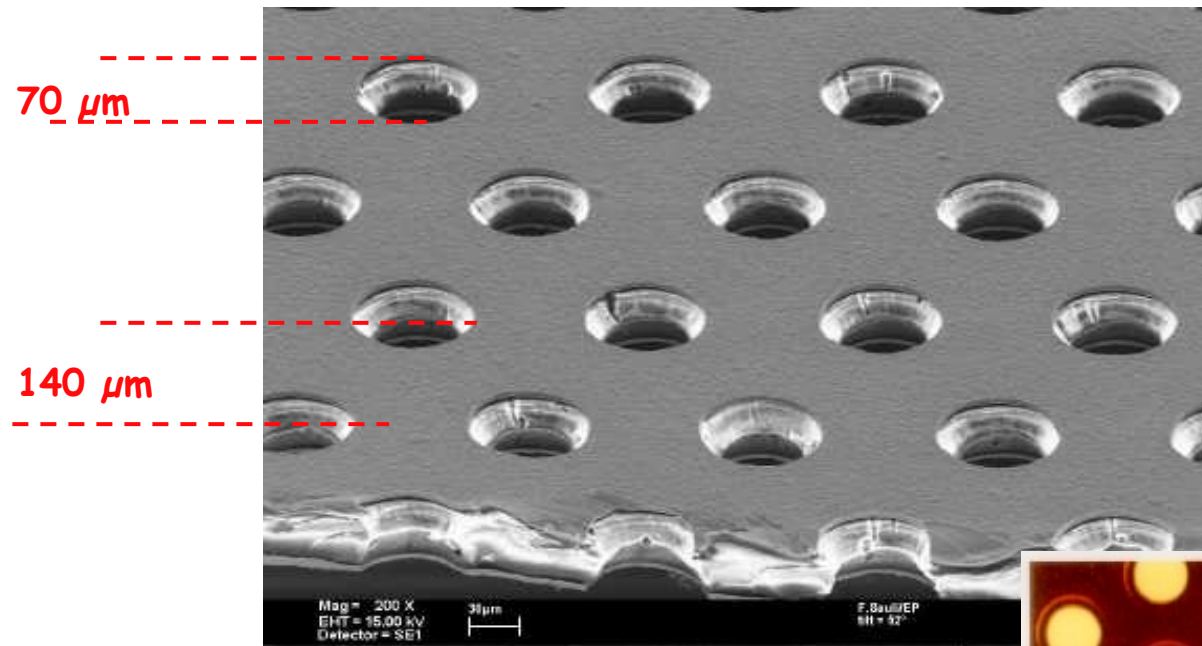
$$V(r) = \frac{CV_0}{2\pi\epsilon_0} \cdot \ln \frac{r}{a}$$

Cylindrical geometry is not the only one able to generate strong electric field:

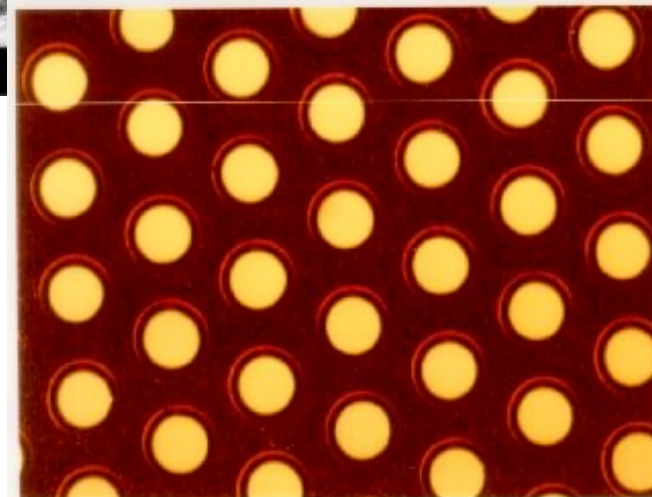
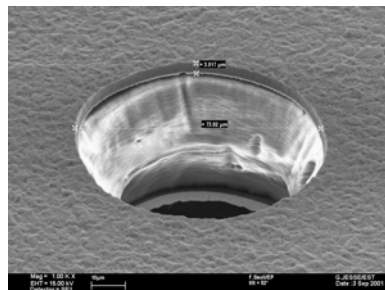


GEM: Gas Electron Multiplier

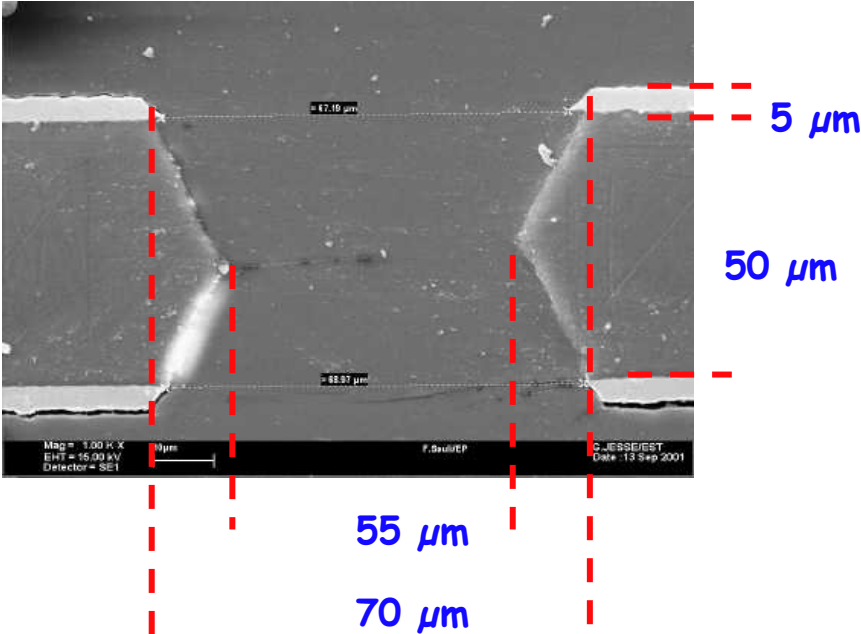
Thin metal-coated polymer foil pierced by a high density of holes (50-100/mm²)
Typical geometry: 5 μm Cu on 50 μm Kapton, 70 μm holes at 140 μm pitch



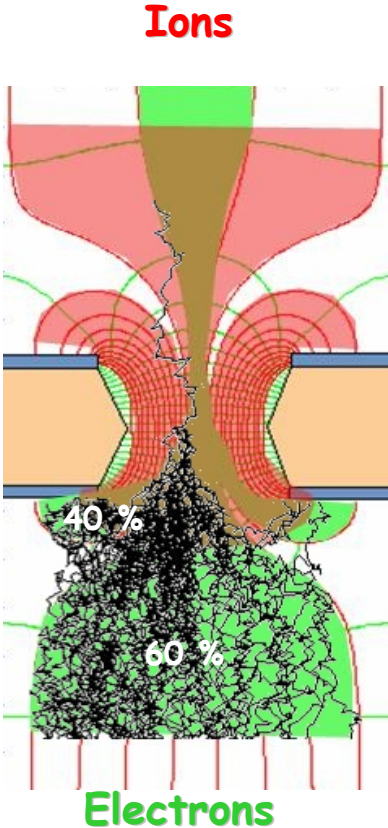
F. Sauli, Nucl. Instrum. Methods A386(1997)531



GEM Principle

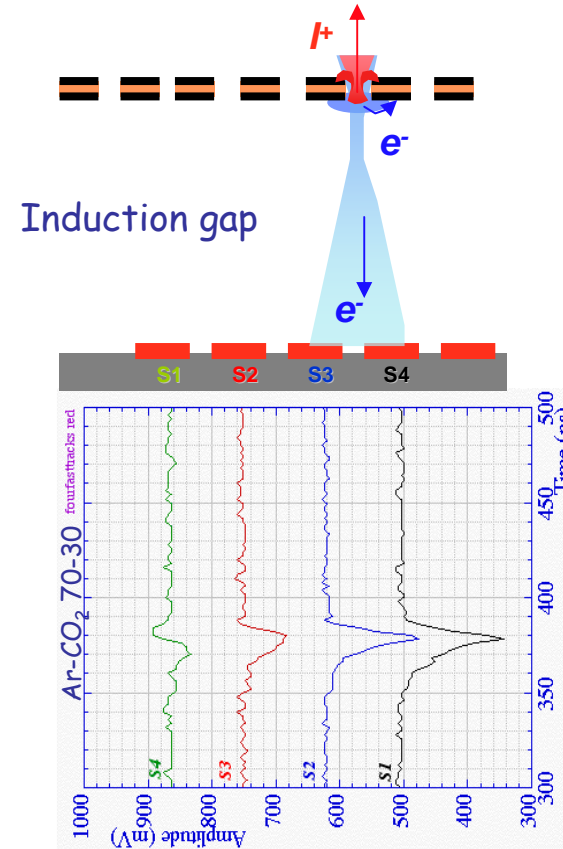
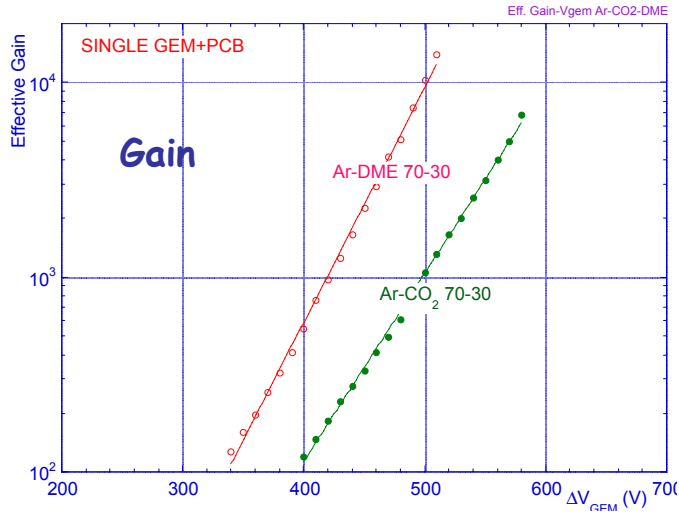


GEM hole cross section

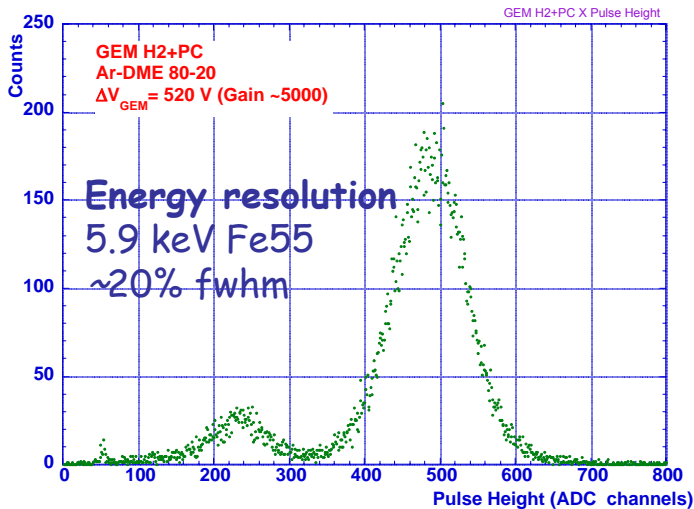


Avalanche simulation

Single GEM Performances



Electrons are collected on patterned readout board.
 A fast signal can be detected on the lower GEM electrode for triggering or energy discrimination.
 All readout electrodes are at ground potential.
 Positive ions partially collected on the GEM electrodes.



GEM Manufacturing

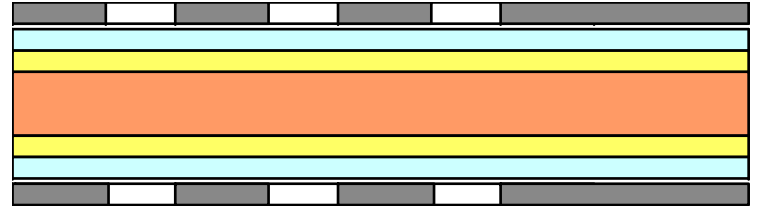
Rui De Oliveira
CERN-EST-DEM



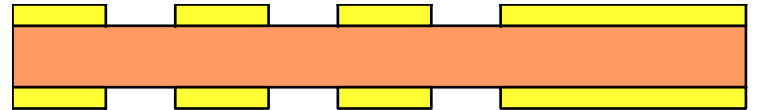
50 μm Kapton
5 μm Cu both sides



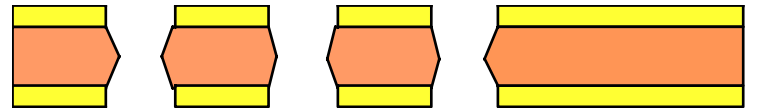
Photoresist coating,
masking and exposure
to UV light



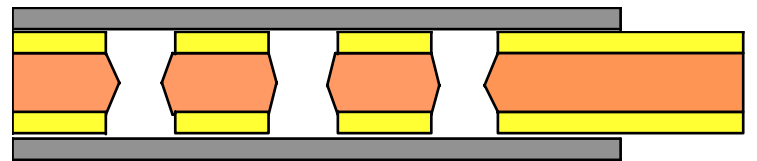
Metal etching



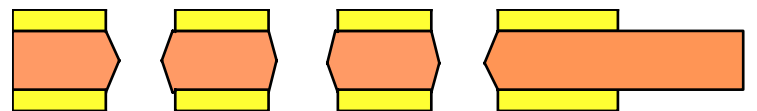
Kapton etching



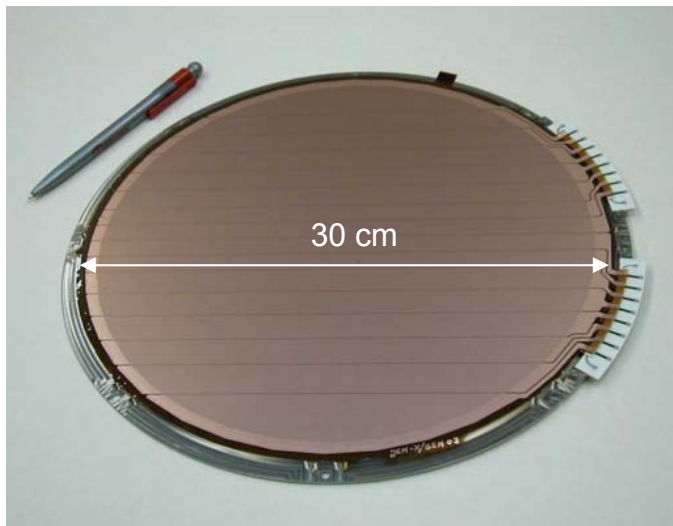
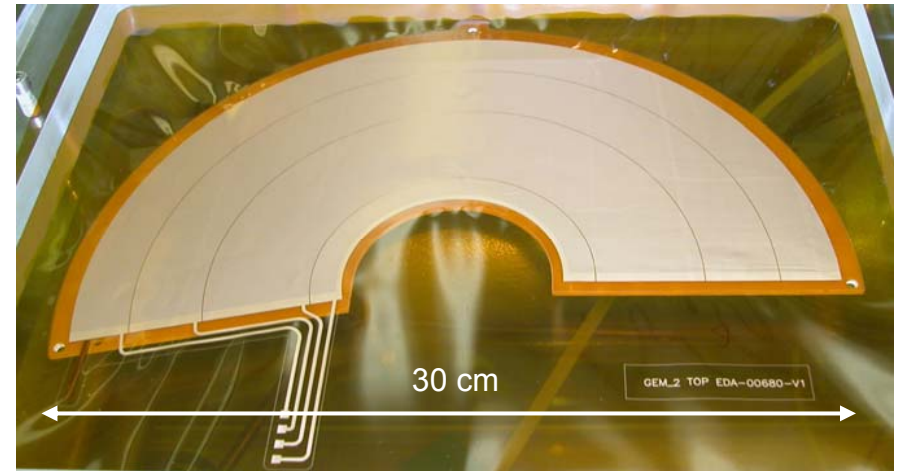
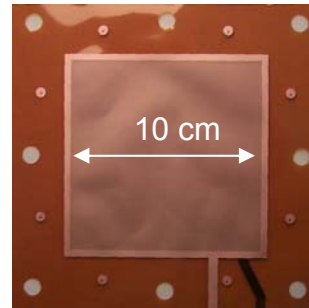
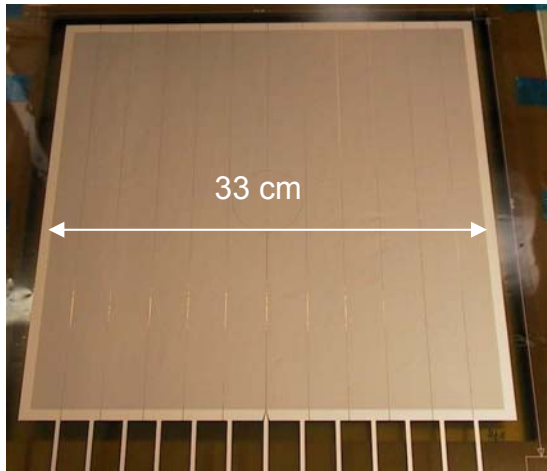
Second masking



Metal etching
and cleaning



GEM Manufacturing



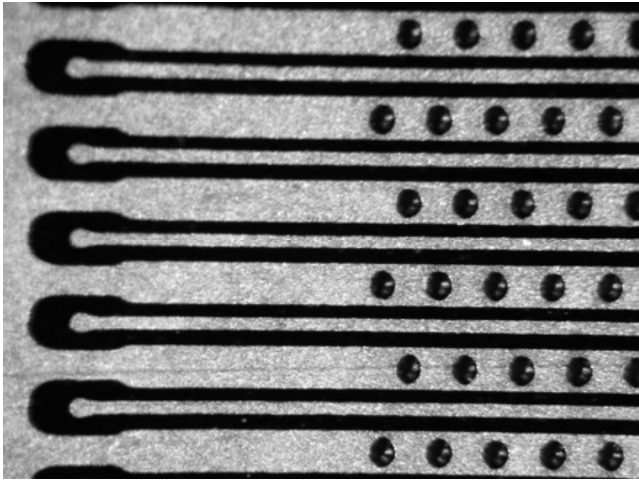
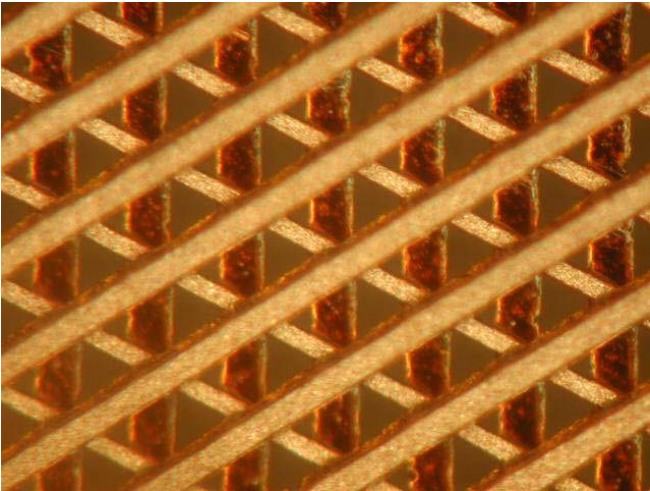
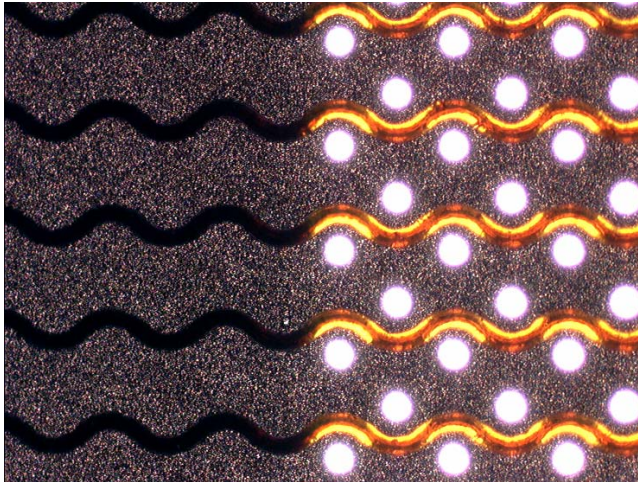
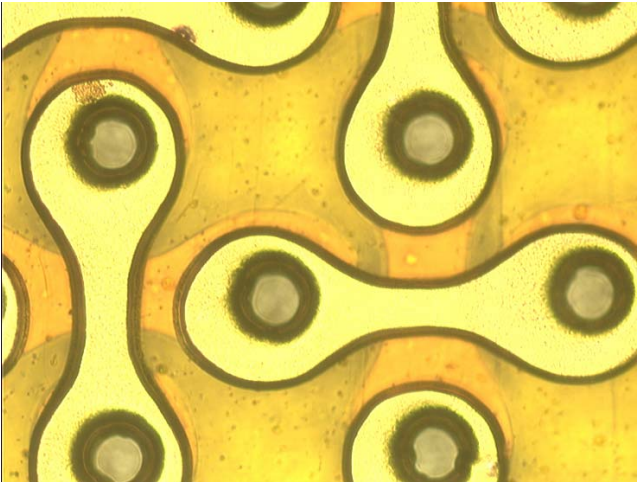
Wide range of shapes and sizes

1500 ÷ 2000 foils manufactured at CERN

1 cm² to 1000 cm²

30-200 μm holes, 50-300 μm pitch

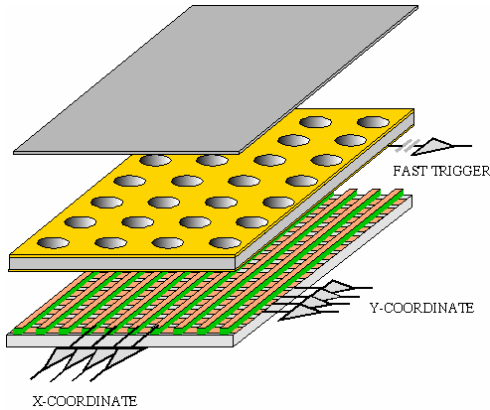
Art of Kapton Etching



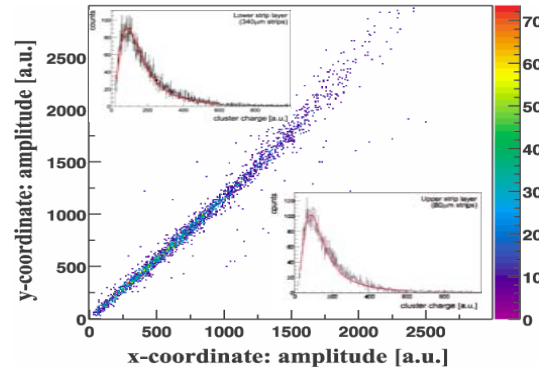
GEM - Gas Electron Multiplier

Full decoupling of the charge amplification structure from the charge collection and readout structure.

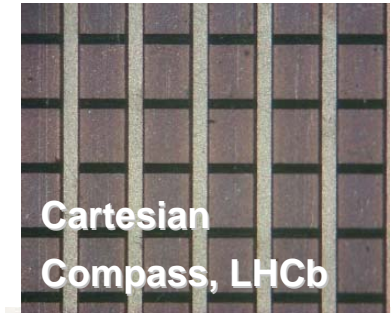
Both structures can be optimized independently !



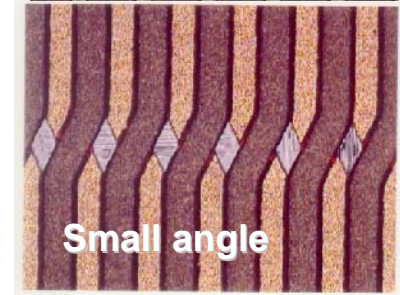
A. Bressan et al, Nucl. Instr. and Meth. A425(1999)254



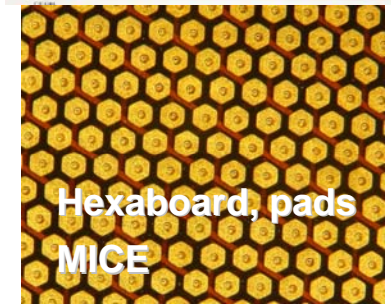
Charge correlation (Cartesian readout)



Cartesian
Compass, LHCb



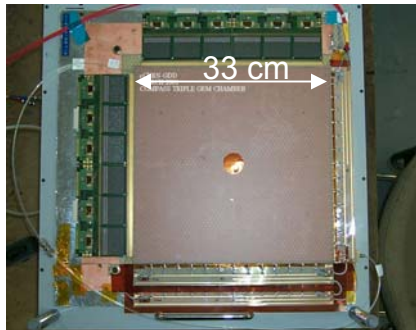
Small angle



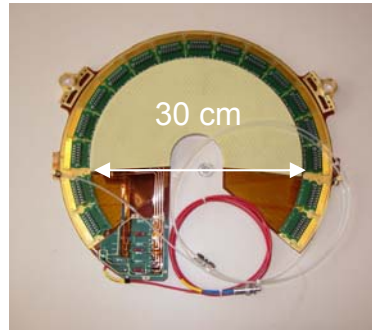
Hexaboard, pads
MICE



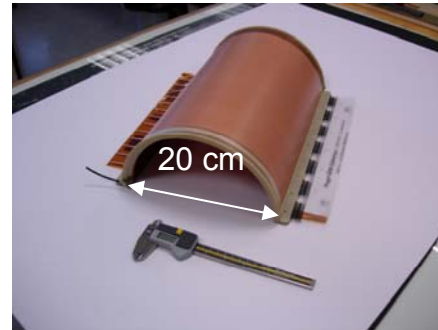
Mixed
Totem



Compass



Totem



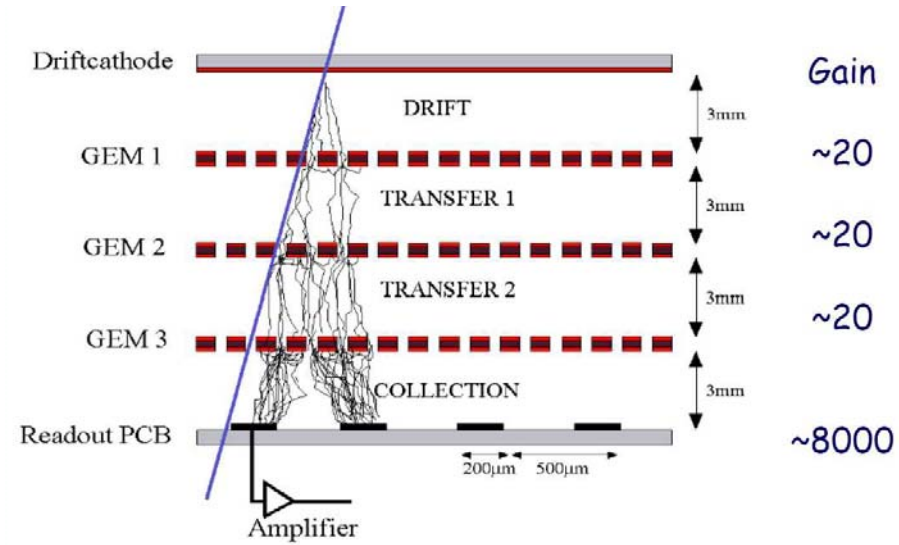
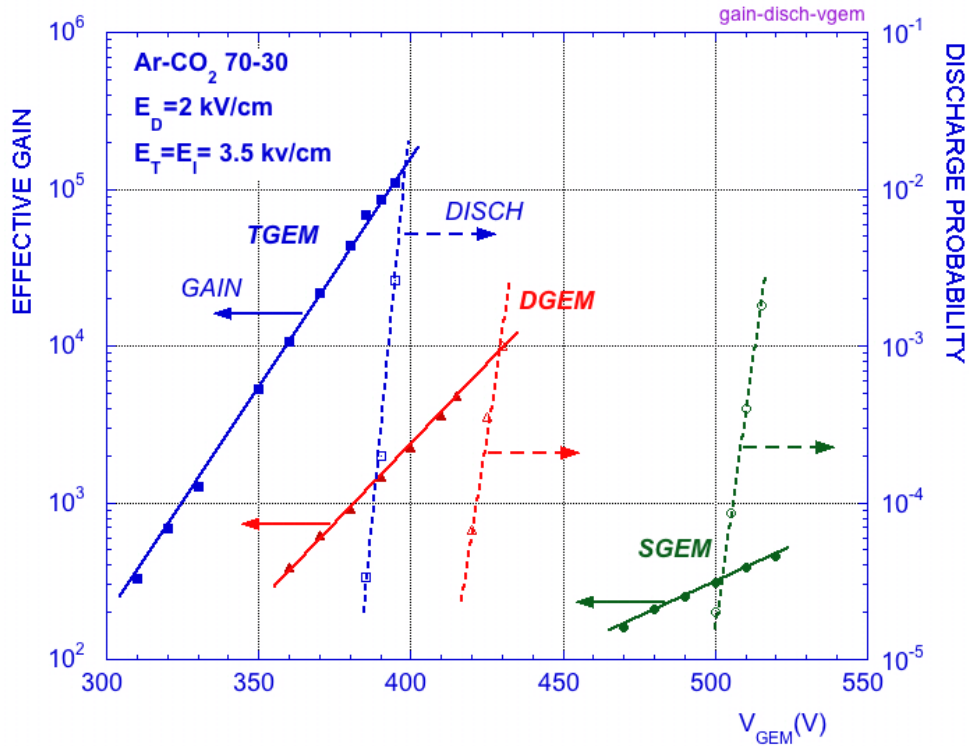
NA49-future

All detectors use three GEM foils in cascade for amplification to minimize discharge probability by reducing field strength.

Multi-GEM Detectors

Discharge Probability on Exposure to 5 MeV Alphas

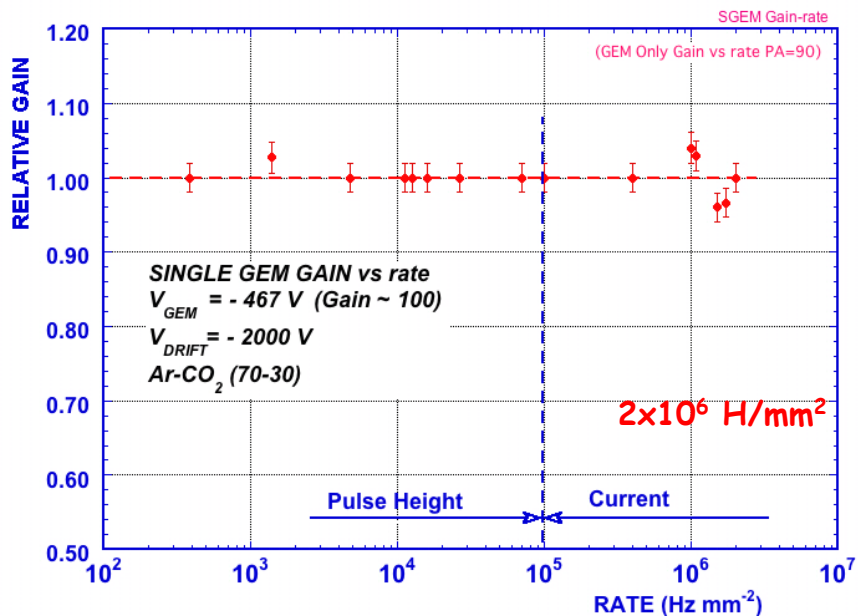
Multiple structures provide equal gain at lower voltage.
 Discharge probability on exposure to α particles is strongly reduced.



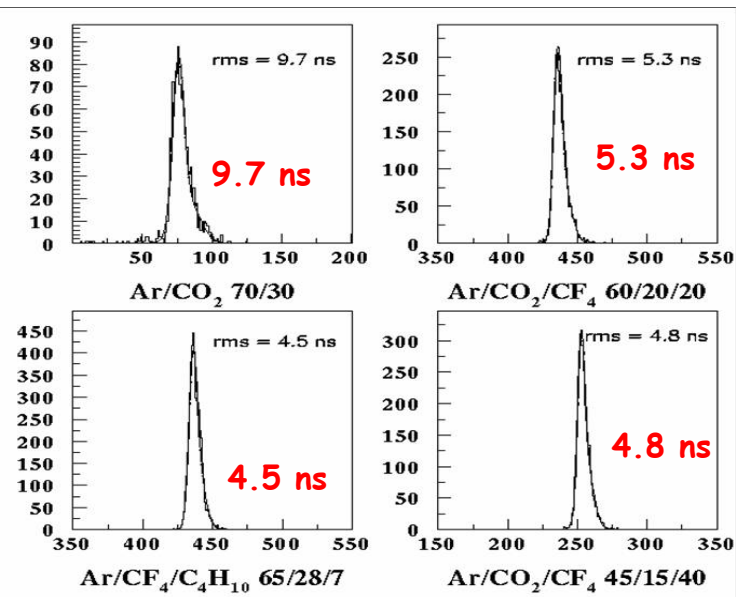
S. Bachmann et al Nucl. Instr. and Meth. A479(2002)294



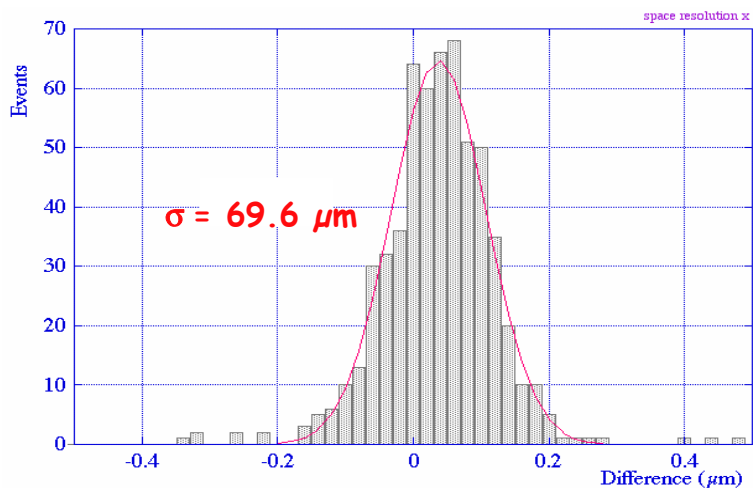
GEM - Gas Electron Multiplier



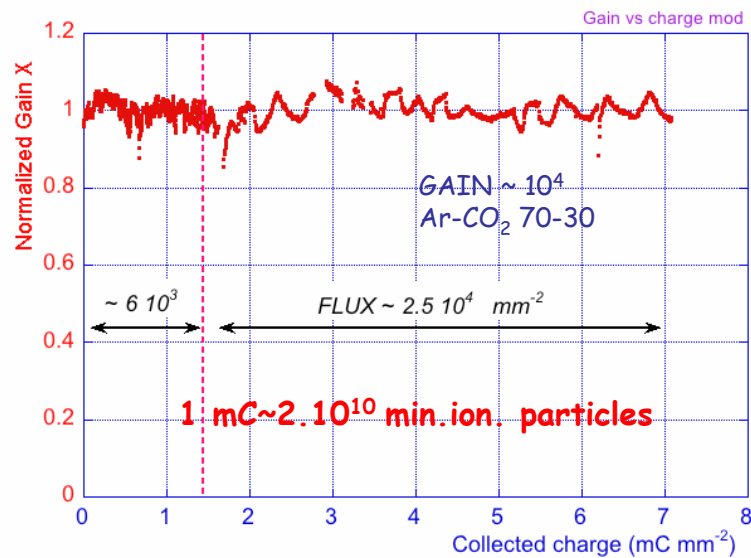
Rate capability



Time resolution



Space resolution

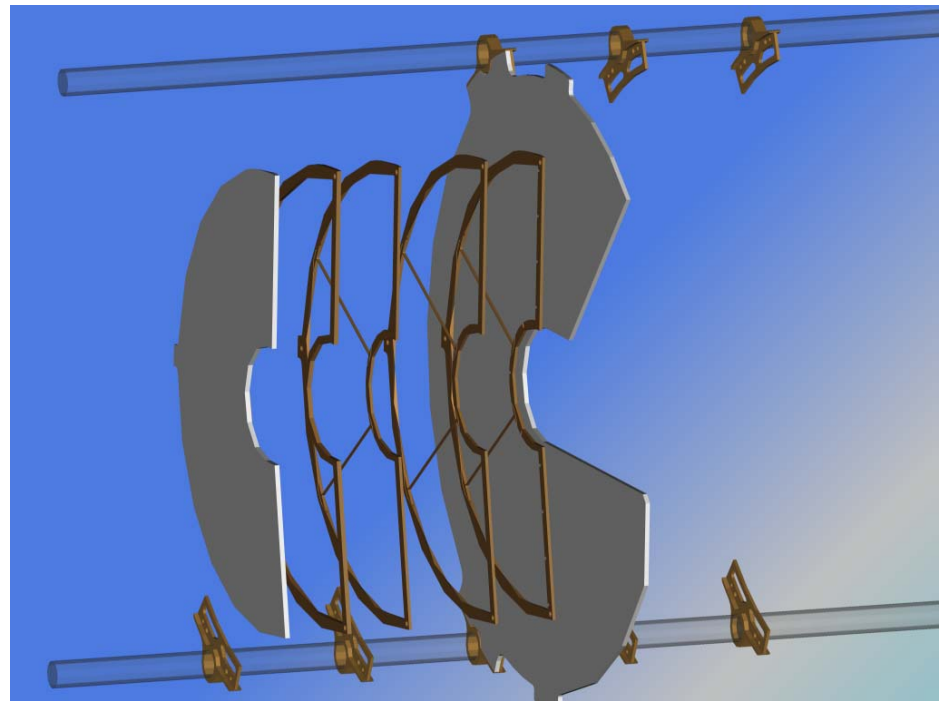
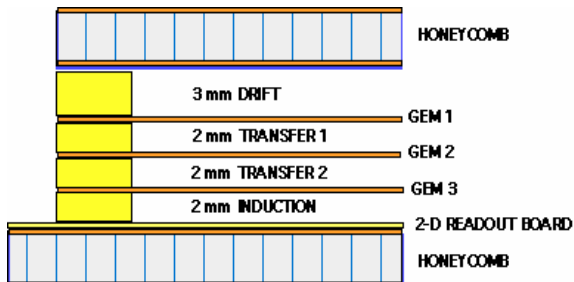
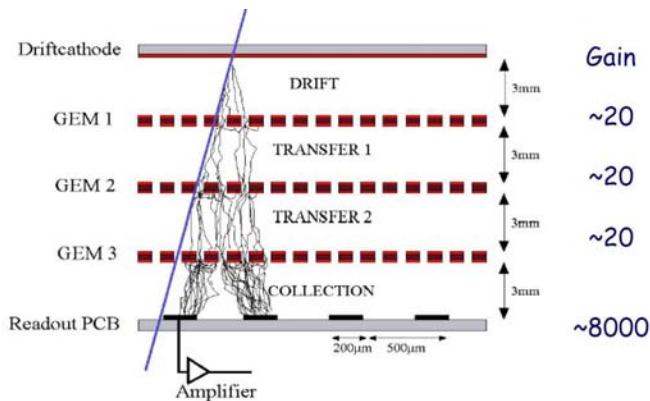


Ageing properties

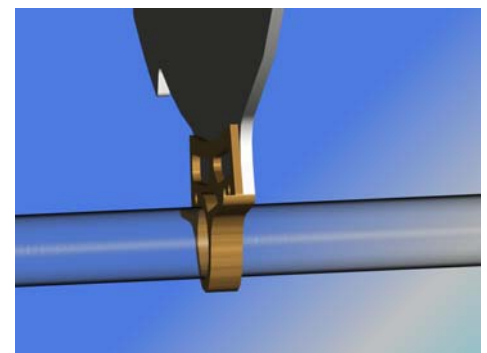
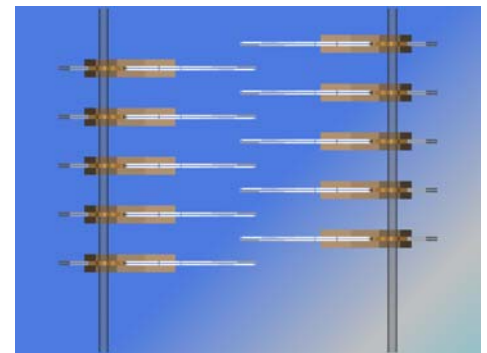
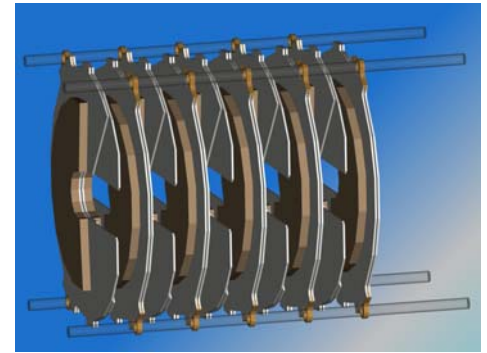
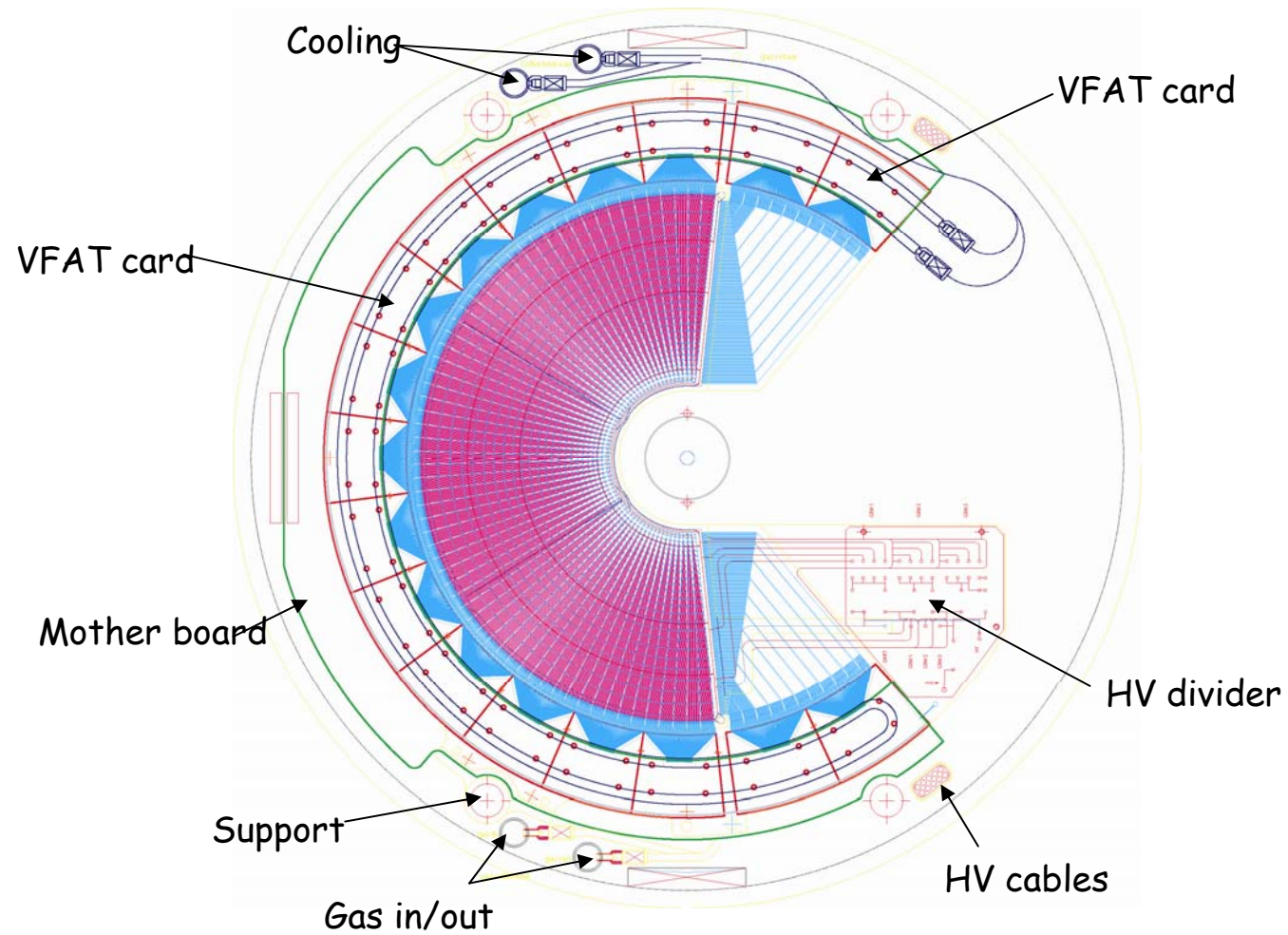
TOTEM GEM : Concept and Design

Detector requirements:

- Rate Capability** - Charge particle rates $10^4 \text{ p mm}^{-2}\text{s}^{-1}$ at $\mathcal{L} = 10^{33} \text{ cm}^{-2}\text{s}^{-1}$
- Ageing** - 1 year of continuous operation $10^{11} \text{ p mm}^{-2} \rightarrow 7 \text{ mC mm}^{-2}$
- Discharges** - at probability of $10^{-12}/\text{part.} \rightarrow 10 \text{ disch. cm}^{-2} \text{ year}^{-1}$
- Time Resolution** - $< 10 \text{ ns}$
- Space Resolution** - $< 100 \mu\text{m}$
- Efficiency** - $> 97 \%$

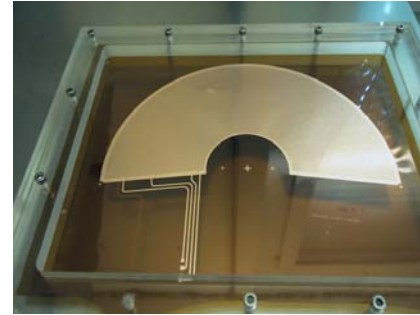
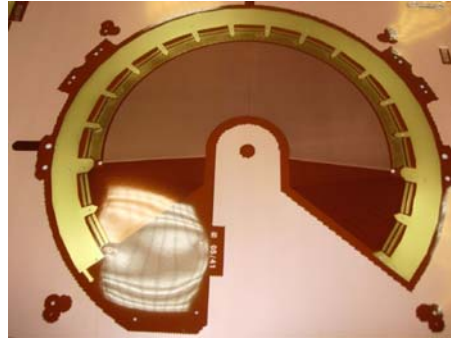


TOTEM GEM Final Detector Module



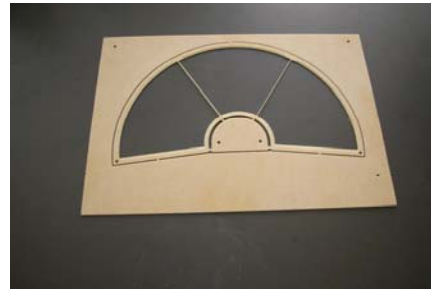
Detector Components

Readout board

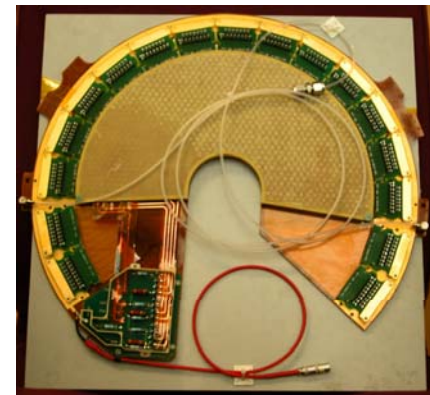


GEM foils

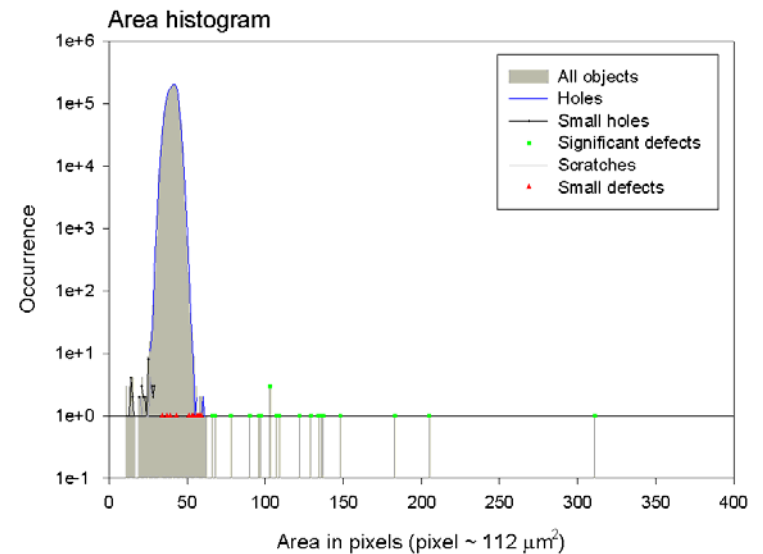
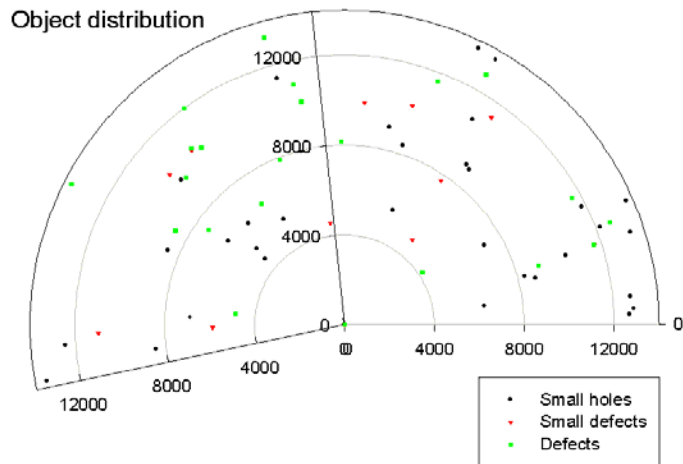
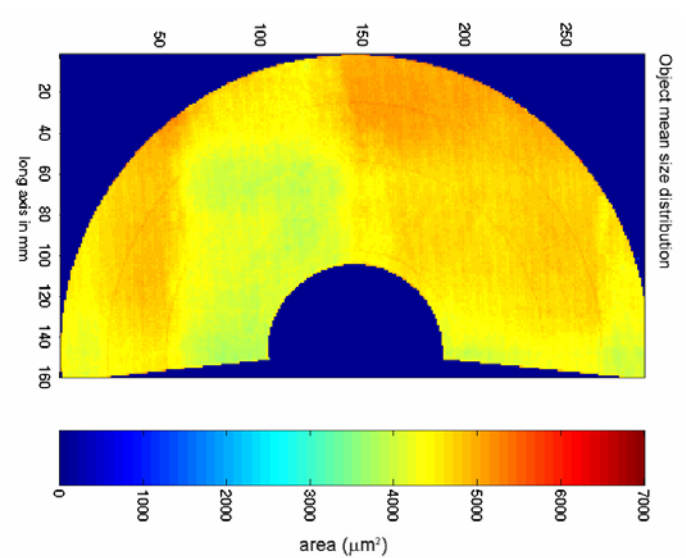
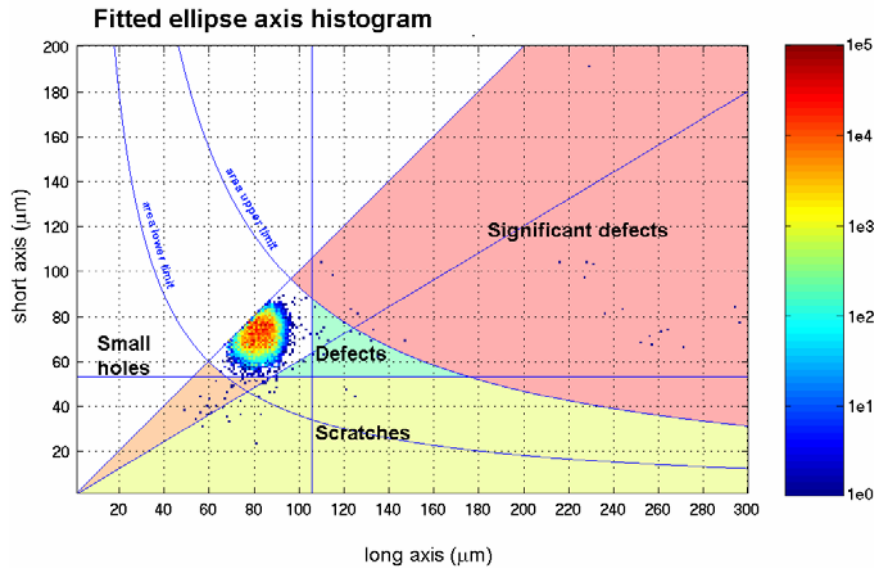
Frames, spacers and supports



HV and electronics

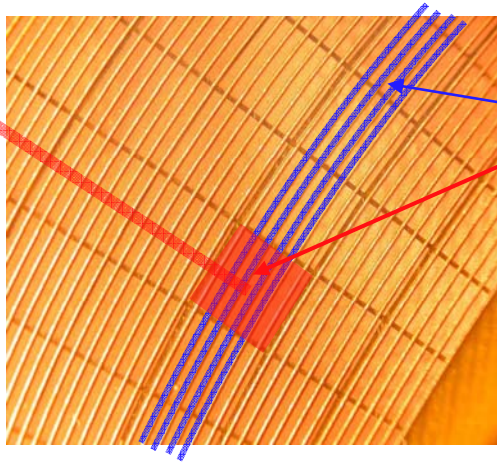


Analysis of defects and hole sizes

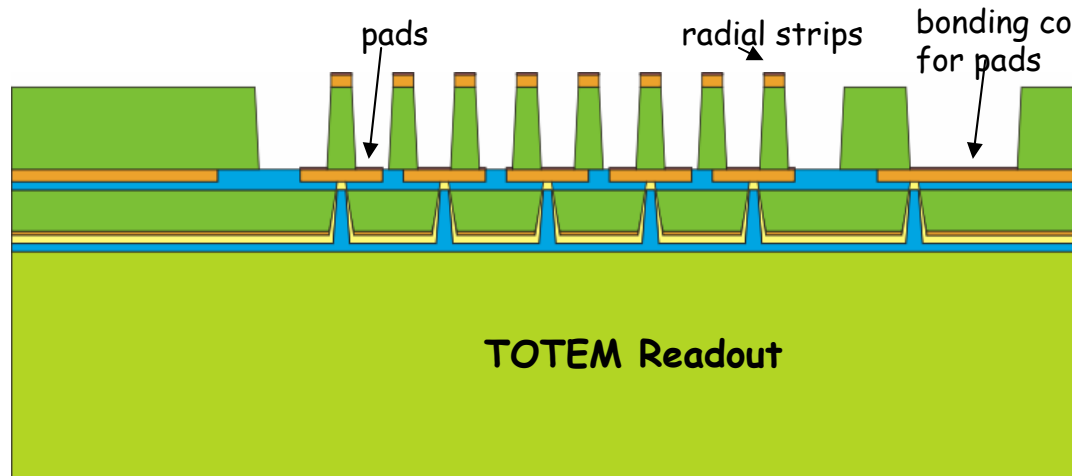
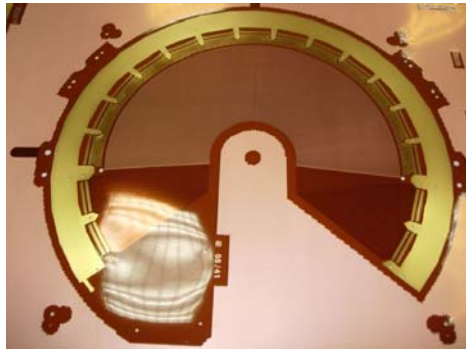
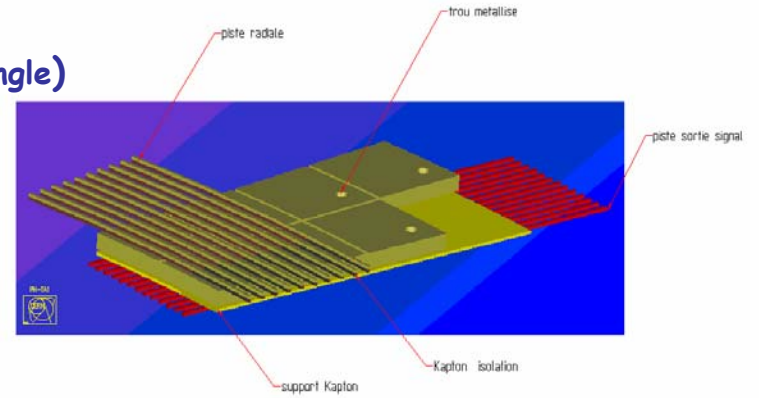


TOTEM GEM - Readout Board

IMAGE DU CIRCUIT DE LECTURE



TOTEM READOUT BOARD:
 Radial strips (accurate track's angle)
 Pad matrix (fast trigger)

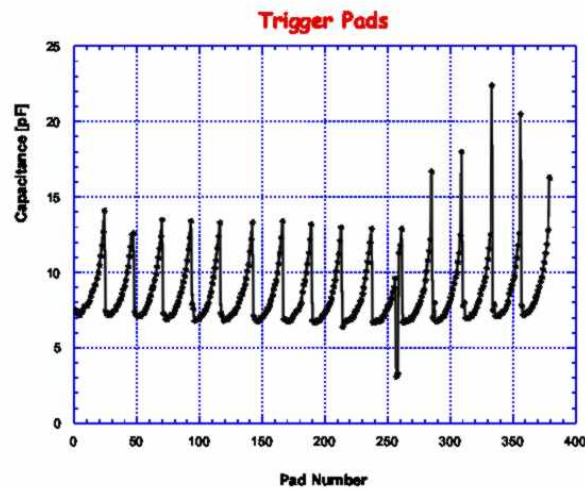
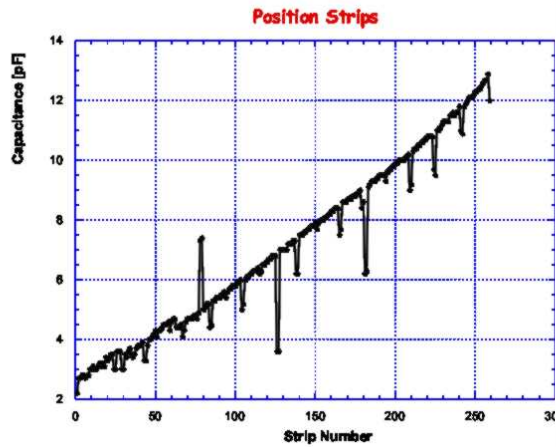
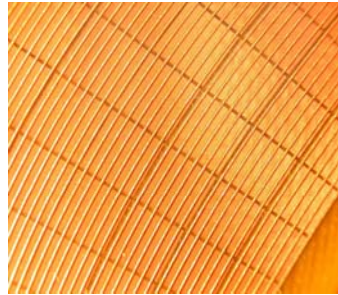
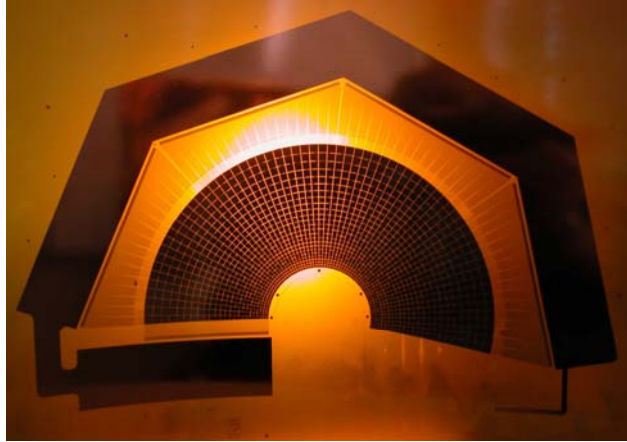


Ni Au
 15 μm Cu
 50 μm Polyimide
 15 μm Cu
 Epoxy glue
 25 μm Polyimide
 5 μm Cu
 10 μm Cu
 Epoxy
 glue

125 μm FR4

TOTEM Readout

TOTEM GEM Readout Board Test



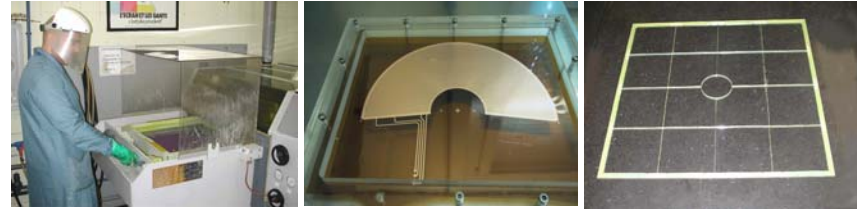
Quality test for continuity and shorts - Capacitance measurement between channels for strips and pads

GEM Detectors Production at CERN

Detector Design



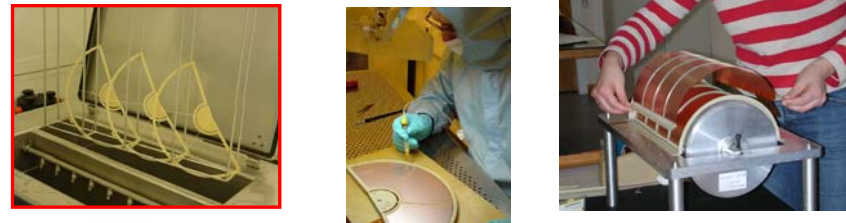
Component Production



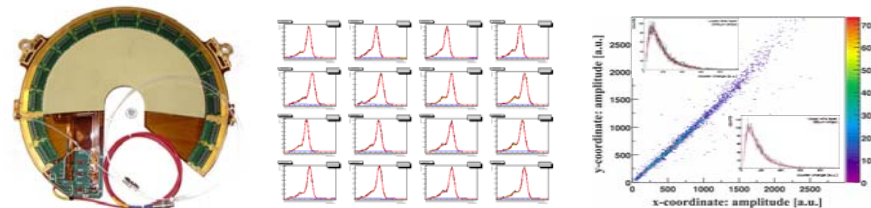
Component Quality Control



Detector Assembly



Detector Test



Staff Training



Perspectives

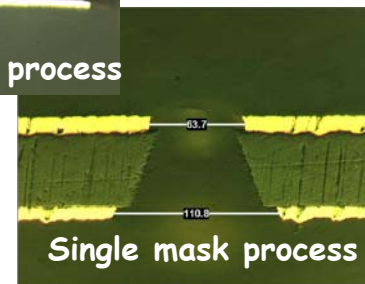
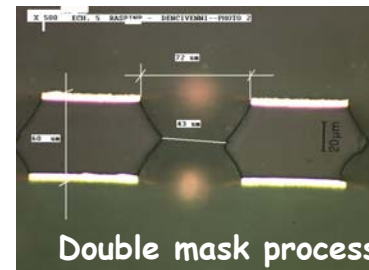
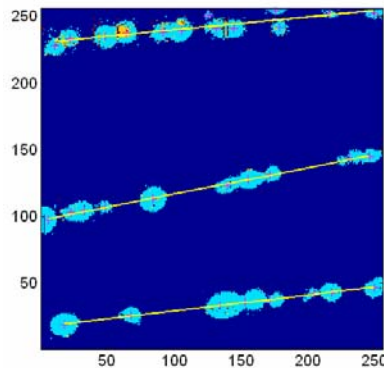
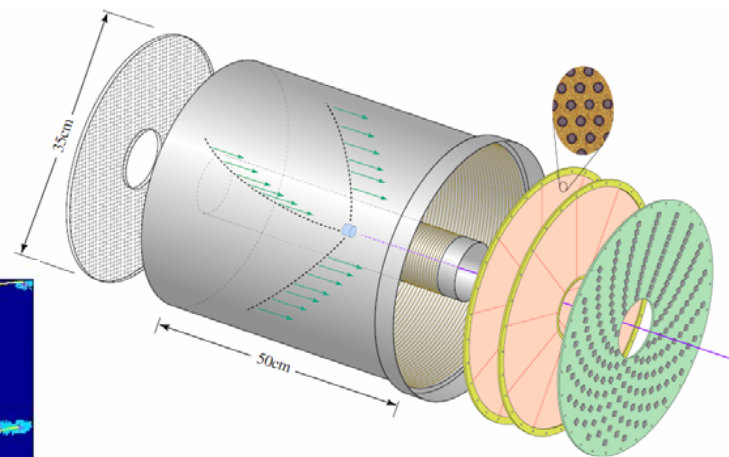
Tracking and triggering (LHCb & TOTEM)
TPC end cap readout (ion feedback reduction)

X-ray radiography
UV light detection
Parallax error free detector
Hadron blind
Neutron detection
Optical GEM
Cryogenic detectors
Two-phase detectors

High resolution detectors integrated with pixel CMOS chips

Non planar large acceptance detectors
Light detectors - mass reduction
New readout structures adopted to experimental needs

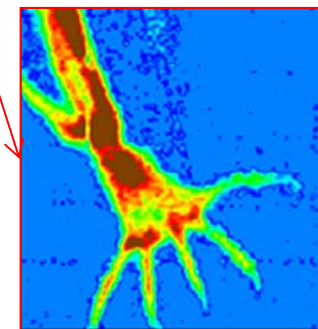
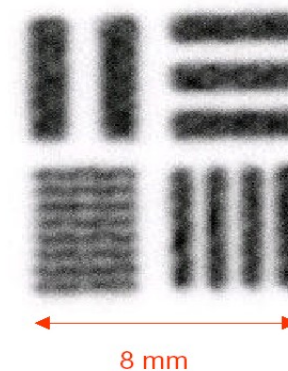
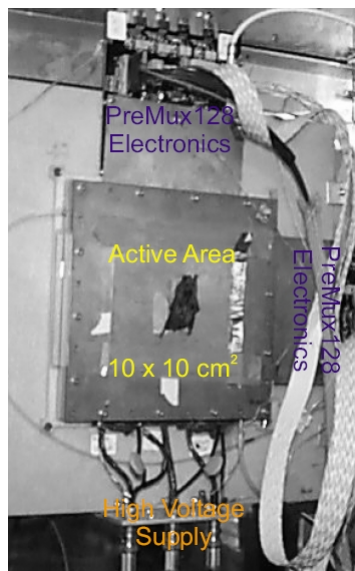
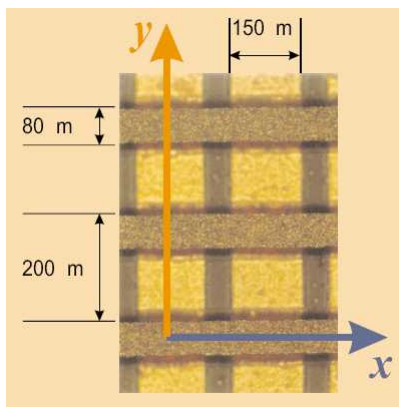
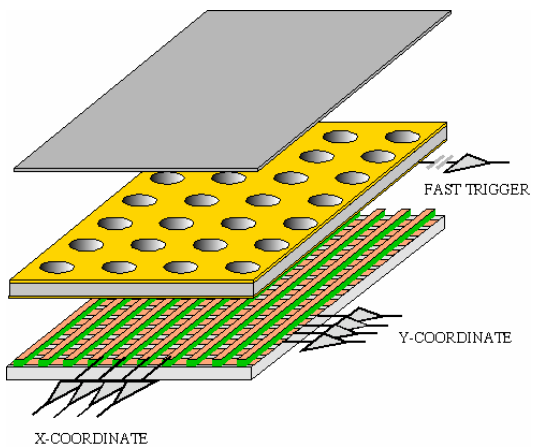
Large size detectors
Industrialization of the mass production



<http://gdd.web.cern.ch/GDD/>



Absorption radiography with GEM (8 keV X-rays)



Trigger from the bottom electrode of GEM.

Absorption radiography with GEM (8 keV X-rays)

